



MPD05N50B

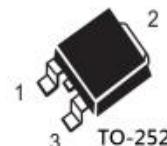
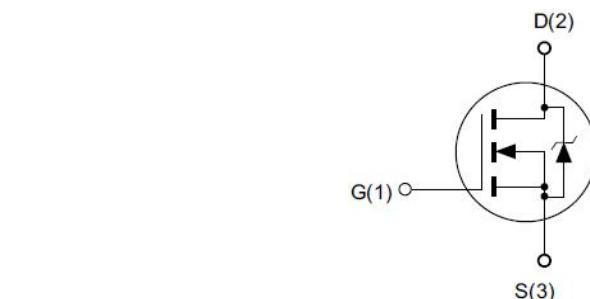
N-Channel Power MOSFET

Features

- ◆ 500V, 5A, $R_{DS(ON)}$ (Typ.) = 2.0Ω@VGS = 10V.
- ◆ Low Crss
- ◆ Fast Switching
- ◆ 100% Avalanche Tested

Application

- ◆ Adaptor
- ◆ Standby Power
- ◆ Switching power supply
- ◆ LED Power



Absolute Maximum Ratings $T_c = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Rating	Unit
V_{DS}	Drain-Source Voltage ^a	500	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-Continuous, $T_c = 25^\circ C$	5	A
	Drain Current-Continuous, $T_c = 100^\circ C$	3.2	A
I_{DM}	Drain Current-Pulsed ^b	20	A
P_D	Maximum Power Dissipation @ $T_J = 25^\circ C$	98	W
dv/dt	Peak Diode Recovery dv/dt ^c	5	V/ns
E_{AS}	Single Pulsed Avalanche Energy ^d	125	mJ
T_J, T_{STG}	Operating and Store Temperature Range	150, -55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Value	Unit
R_{eJc}	Thermal Resistance, Junction to Case	1.27	°C/W
R_{eJA}	Thermal Resistance, Junction to Ambient	60	°C/W

Electrical Characteristics $T_J = 25^\circ C$ unless otherwise noted

■ Off Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	500	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 500V, V_{GS} = 0V$	-	-	1	μA
I_{GSS}	Forward Gate Body Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 30V$	-	-	± 100	nA



MPD05N50B

N-Channel Power MOSFET

■ On Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	2	3.1	4	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10V$, $I_D = 2.5A$	-	2.0	2.5	Ω
g_{fs}	Forward Transconductance	$V_{DS}=15V$, $I_D=2.5A$	-	3.9	-	S

■ Dynamic Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
R_g	Gate Resistance	$f = 1.0MHz$	-	2.1	-	Ω
C_{iss}	Input Capacitance		-	503	-	pF
C_{oss}	Output Capacitance		-	41	-	pF
C_{rss}	Reverse Transfer Capacitance		-	2.3	-	pF

■ On Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 250V$, $I_D = 5A$, $V_{GS}=10V$, $R_g=10\Omega$	-	8	-	ns
t_r	Turn-On Rise Time		-	22	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	17	-	ns
t_f	Turn-Off Fall Time		-	22	-	ns
Q_g	Total Gate Charge	$V_{DS} = 400V$, $I_D = 5A$, $V_{GS} = 10V$	-	10.7	-	nC
Q_{gs}	Gate-Source Charge		-	3.9	-	nC
Q_{gd}	Gate-Drain Charge		-	2.4	-	nC

■ Drain-Source Diode Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
I_s	Drain-Source Diode Forward Continuous Current	$V_{GS} = 0V$	-	-	5	A
I_{SM}	Maximum Pulsed Current	$V_{GS} = 0V$	-	-	20	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0V$, $I_s = 5A$	-	0.86	1.15	V
T_{rr}	Body Diode Reverse Recovery Time	$I_s=5A$, $V_{GS} = 0V$ $dI_F/dt=100A/us$	-	315	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	1236	-	nC

Notes:

- $T_J=+25^\circ C$ to $+150^\circ C$
- Repetitive rating; pulse width limited by maximum junction temperature.
- $I_{SD} = 5A$, $dI_F/dt \leq 100A/us$, $V_{DD} \leq BV_{DS}$, Start $T_J=25^\circ C$.
- $L = 10mH$, $V_{DD}=50V$, $I_{AS} = 5A$, $R_G=25\Omega$ Starting $T_J=25^\circ C$.

Characteristic Curve

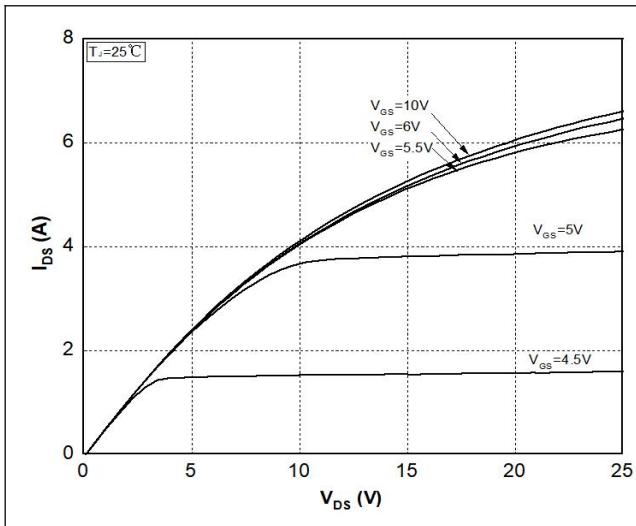


Figure 1. Typical Output Characteristics

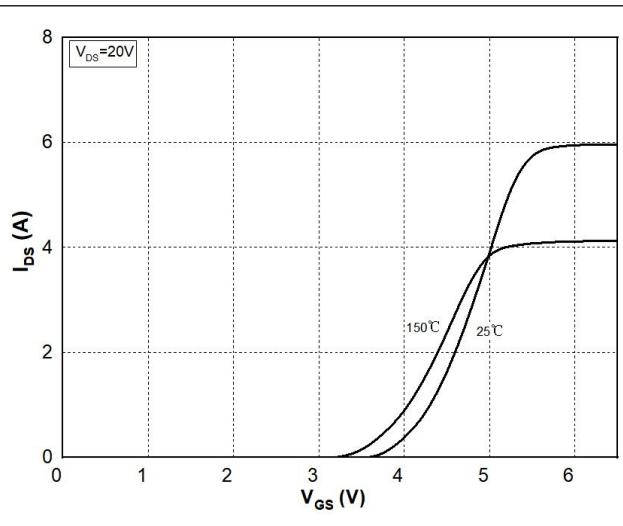


Figure 2. Typical Transfer Characteristics

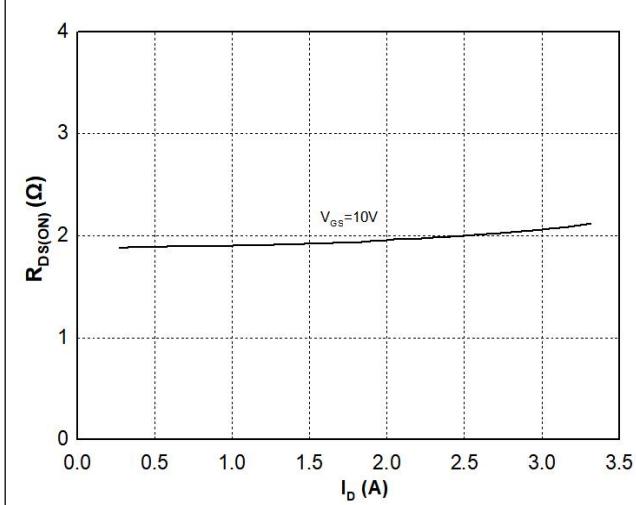


Figure 3. On- Resistance vs. Drain Current

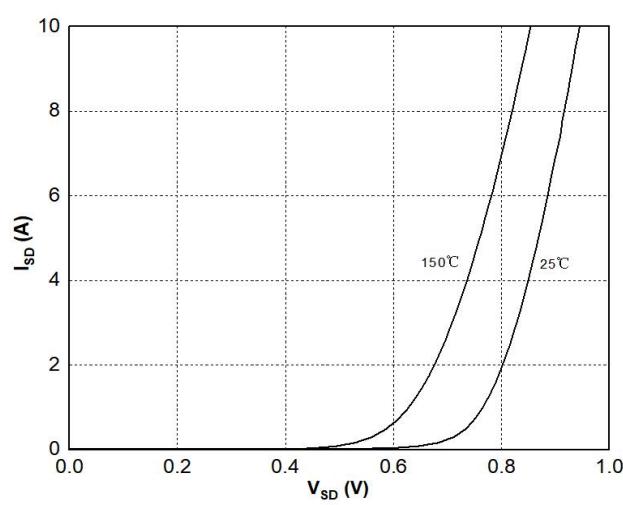


Figure 4. Body-Diode Characteristics

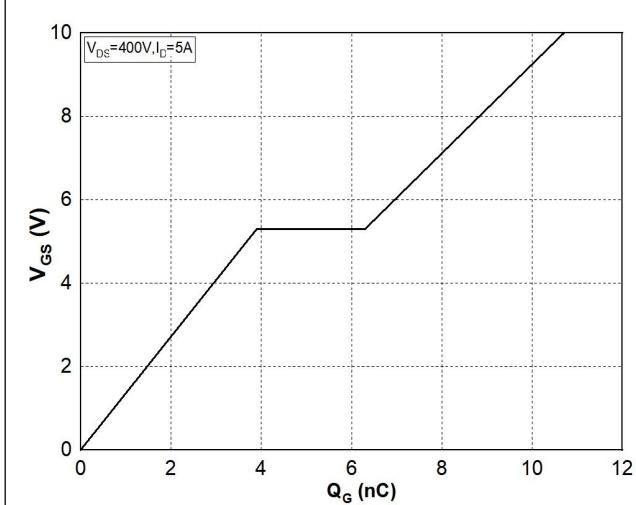


Figure 5. Gate-Charge Characteristics

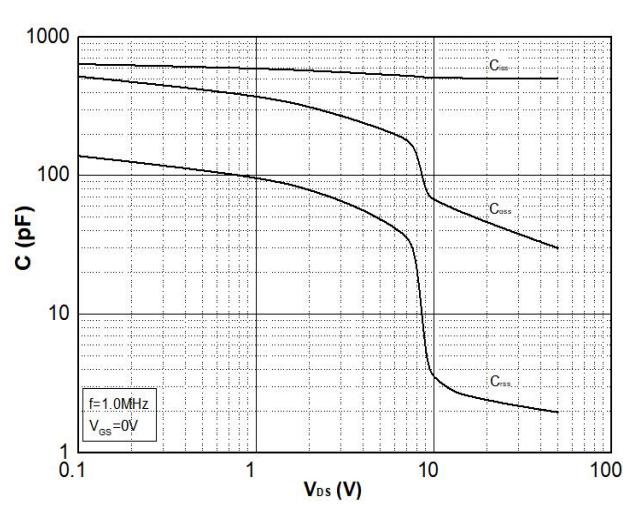
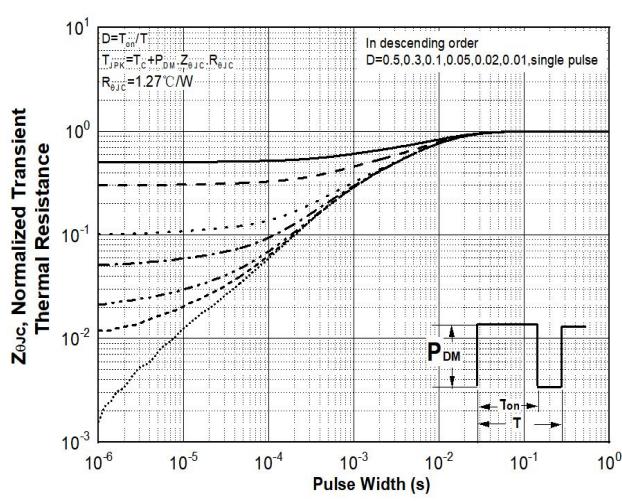
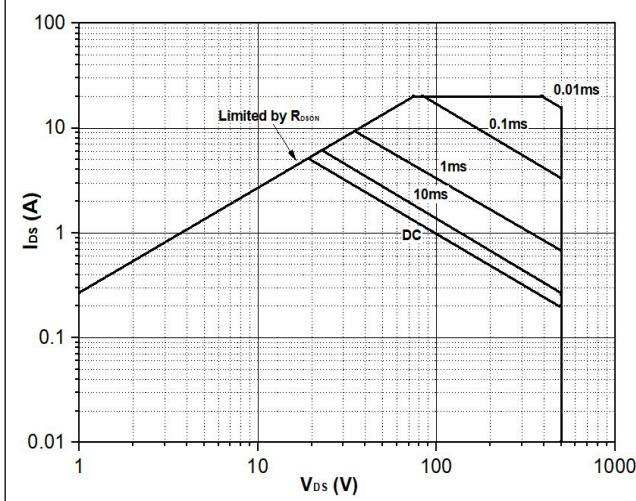
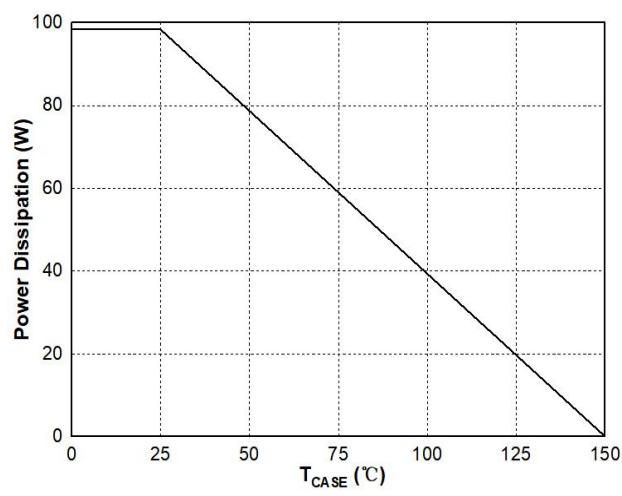
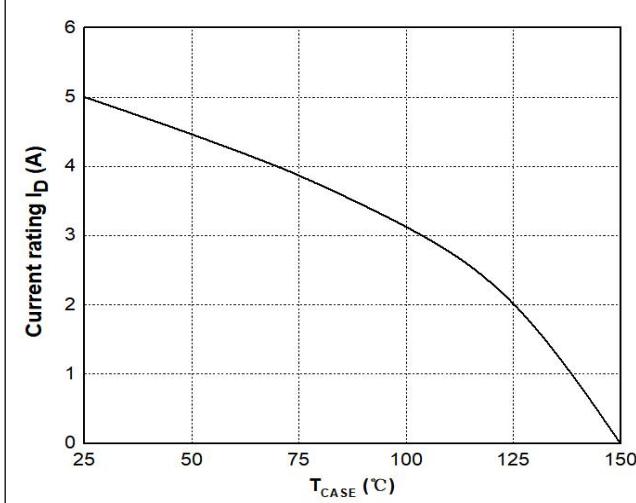
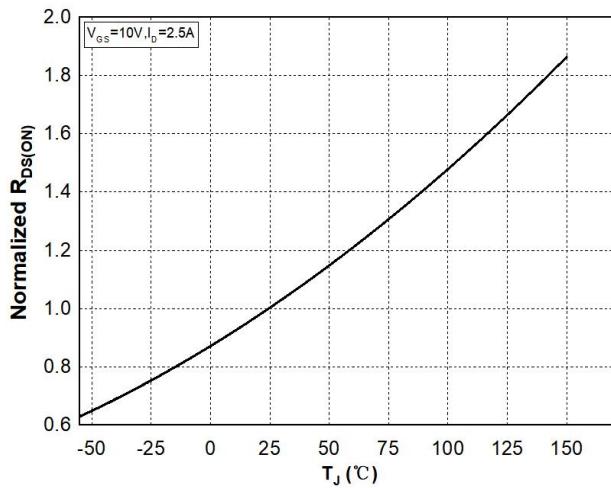
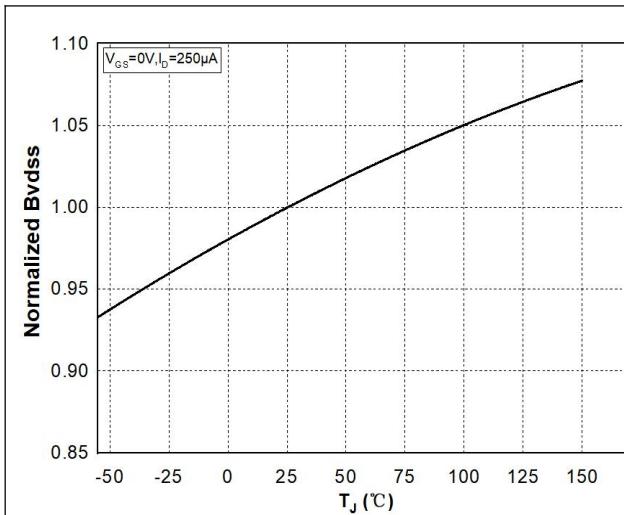


Figure 6. Capacitance Characteristics

■ Characteristic Curve



■ Package Information

TO-252

